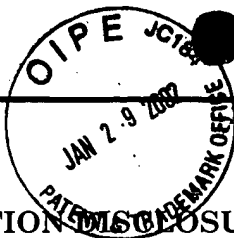


FORM PTO-1449



INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

(use as many sheets as necessary)

Attorney Docket Number	39943/PAN/C715
Application Number	09/871,492
Filing Date	May 31, 2001
Applicant(s)	Kent D. Choquette, et al.
Group Art Unit	2881
Examiner Name	To be Assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Mew</i>	5,719,894	02/1998	Jewell et al.	372	45	
	5,719,895	02/1998	Jewell et al.	372	45	
	5,805,624	09/1998	Yang et al.	372	45	
	5,825,796	10/1998	Jewell et al.	372	45	
	5,903,589	05/1999	Jewell	372	46	
	5,912,913	06/1999	Kondow et al.	372	45	
	5,936,266	08/1999	Holonyak, Jr. et al.	257	106	
	5,960,018	09/1999	Jewell et al.	372	45	
<i>v</i>	6,014,395	01/2000	Jewell	372	45	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
<i>Mew</i>	HEI 5 [1993]-297128	06/1995	Japan	3	18	X	

OTHER DOCUMENTS

EXAMINER INITIALS	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
<i>Mew</i>	J. BOUCART et al., 1-mW CW-RT Monolithic VCSEL at 1.55 μ m, IEEE PHOTONICS TECHNOLOGY LETTERS, June 1999, pp. 629-631, Vol. II, No. 6
	SHIRO SAKAI et al., Band Gap Energy and Band Lineup of III-V Alloy Semiconductors Incorporating Nitrogen and Boron, Jpn. J. Appl. Phys., October 1993, pp. 4413-4416, Vol. 32 Part 1, No. 10
<i>v</i>	M. C. LARSON et al., GaInNAs-GaAs Long-Wavelength Vertical-Cavity Surface-Emitting Laser Diodes, IEEE PHOTONICS TECHNOLOGY LETTERS, February 1998, pp. 188-190, Vol. 10, No. 2

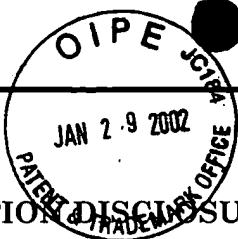
EXAMINER SIGNATURE	<i>Matthew Wanner</i>	DATE CONSIDERED	12/11/02
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OTHER DOCUMENTS

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<i>MEW</i>	MASAHIKO KONDOW et al., Gas-Source Molecular Beam Epitaxy of GaN _x As _{1-x} Using a N Radical as the N Source, Jpn. J. Appl. Phys., August 1994, pp. 1056-1058, Vol. 33, Part 2, No. 8A
<i>MEW</i>	MASAHIKO KONDOW et al., Room-Temperature Pulsed Operation of GaInN As Laser Diodes with Excellent High-Temperature Performance, Jpn. J. Appl. Phys., November 1996, pp. 5711-5713, Vol. 35, Part 1, No. 11

EXAMINER SIGNATURE	<i>Matthew E. Wornen</i>	DATE CONSIDERED	<i>12/11/02</i>
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Substitute for PTO-1449.A/B

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Applicant(s)	Kent D. Choquette, et al.
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EXAMINER INITIALS	Cite No. ¹	DOCUMENT NUMBER Number - kind code ² . (If known)	PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	Cite No. ¹	Foreign Patent Document Country Code ³ - Number ⁴ . Kind Code ⁵ (If known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T ⁶ (✓)
Mew		EP 0 822 630 A1	02-04-1998	Hewlett-Packard Company	
		WO 98/07218	02-19-1998	W.L. Gore & Associates, Inc.	

OTHER DOCUMENTS

EXAMINER INITIALS	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		LEAR K L ET AL. "High-frequency modulation of oxide-confined vertical cavity surface emitting lasers" ELECTRONICS LETTER, IEE STEVENAGE, GB, vol. 32, no. 5, 29 February 1996, pages 457-458
		OHNOKI N ET AL. "Super-lattice AlAs/AlInAs for lateral-oxide current confinement in InP-based lasers" JOURNAL OF CRYSTAL GROWTH, NORTH-HOLLAND PUBLISHING CO. AMSTERDAM, NL, vol. 195, no. 1-4, 15 December 1998, pages 603-608

EXAMINER SIGNATURE	Matthew E. Warren	DATE CONSIDERED	
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